## IN THE CLAIMS:

Rewrite the pending claims and add new claims as follows:

- 1. (Original) A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover contains hydroxylamine and at least one alkanolamine wherein said hydroxylamine and said alkanolamine are present in sufficient amounts to remove a resist from a substrate.
- 2. (Original) The method of claim 1 wherein the resist includes a polyimide.
- (Original) The method of claim 1 wherein the resist includes resist that has been exposed to a process selected from plasma etching, reactive ion etching and ion milling.
- 4. (Original) The method of claim 1 wherein said remover further includes a chelating agent.
- 5. (Currently amended) The method of claim 1 wherein said hydroxylamine and said <u>at</u>

  <u>least one alkanolamine solvent</u> are maintained separately and are combined at the

  process location where said remover contacts said resist.
- 6. (Currently amended) The method of claim 5 wherein a chelating agent is maintained separately and combined with added to the remover after combining said hydroxylamine and said at least one alkanolamine at said process location.
- 7. (Original) The method of claim 1 wherein said remover contacts said resist during the fabrication of a submicron integrated circuit.
- 8. (Currently amended) The method of claim 1 wherein said hydroxylamine is present in an amount from at least about 2.5% to about 45-25% by weight neat.
- 9. (Original) The method of claim 8 wherein said remover further contains a chelating agent.
- 10. (Original) The method of claim 9 wherein said remover further contains at least one polar solvent.

- 11. (Original) The method of claim 8 wherein said at least one alkanolamine is selected from the group consisting of monoamines, diamines and triamines.
- 12. (Currently amended) A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover comprises from about 2.5% to about 45-25% by weight neat hydroxylamine, at least one alkanolamine, and at least one polar solvent wherein said remover contacts said substrate having a resist thereon after a process of etching.
- 13. (Currently amended) The method of claim 12 wherein said contacting occurs after the process of etching remover comprises about 8.75% to about 20% by weight neat hydroxylamine, at least one alkanolamine selected from the group consisting of monoamines, diamines, and triamines, at least one polar solvent, and a chelating agent.
- 14. (Original) The method of claim 1 wherein the aqueous remover contains at least about 70% water.
- 15. (Original) The method of claim 12 wherein the aqueous remover contains at least about 70% water.
- 16. (Original) The method of claim 12 wherein said remover further includes a chelating agent.
- 17. (Original) The method of claim 4 wherein said chelating agent is an organic acid.
- 18. (Original) The method of claim 16 wherein said chelating agent is an organic acid.
- 19. (Currently amended) A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover comprises a hydroxylamine of the formula:

$$R_1$$
 $N \longrightarrow O \longrightarrow R_3$ 

wherein  $R_1$ , and  $R_2$ , and  $R_3$  are independently hydrogen; a hydroxyl group; optionally a substituted  $C_1$ - $C_6$  straight, branched or cyclo alkyl, alkenyl, or alkynyl group; optionally a

substituted acyl group, straight or branched alkoxy group, amidyl group, carboxyl group, alkoxyalkyl group, alkylamino group, alkylsulfonyl group, or sulfonic acid group, or the salt of such compounds; and R<sub>3</sub> is hydrogen; optionally a substituted C<sub>1</sub>-C<sub>6</sub> straight, branched or cyclo alkyl, alkenyl, or alkynyl group; optionally a substituted acyl group, straight or branched alkoxy group, amidyl group, carboxyl group, alkoxyalkyl group, alkylamino group, alkylsulfonyl group, or sulfonic acid group, or the salt of such compounds; at least one alkanolamine selected from the group consisting of monoamines, diamines and triamines; at least one polar solvent; and at least one chelating agent.

20. (Original) The method of claim 19 wherein said contacting occurs after the process of etching.